

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Original) A semiconductor device comprising:
  - a semiconductor substrate;
  - a first insulating film formed above the semiconductor substrate and having a relative dielectric constant of 3.8 or less;
  - a conductor which covers a side face of the first insulating film at least near four corners of the semiconductor substrate, and at least an outer side face of which has a conductive barrier layer; and
  - a second insulating film covering the outer side face of the conductor and having a relative dielectric constant of over 3.8.
2. (Currently Amended) A semiconductor device as set forth in claim 1, wherein the conductive barrier layer that the conductor has contains one kind selected from a group consisting of titanium (Ti), tantalum (Ta), zirconium (Zr), and tungsten (W), and the conductor contains as a major component one kind selected from a group consisting of copper (Cu), aluminum (Al), and tin (Sn).
- 3.-6. (Cancelled)
7. (Original) A semiconductor device as set forth in claim 1,

wherein the second insulating film also covers an upper side of the first insulating film, the semiconductor device further comprising

a conductor pattern passing through the second insulating film positioned on the upper side of the first insulating film.

8. (Cancelled )

9. (Original) A semiconductor device as set forth in claim 7, further comprising a conductive pattern buried in the first insulating film.

10. (Cancelled )

11. (Original) A semiconductor device as set forth in claim 1, wherein the first insulating film is constituted of a plurality of layers.

12. (Cancelled )

13. (Original) A semiconductor device as set forth in claim 1, wherein the conductor is formed in a ring shape covering an entire side face of the first insulating film.

14. (Cancelled )

15. (Original) A semiconductor device as set forth in claim 1, wherein the second insulating film is at least one kind selected from a group consisting of silicon oxide ( $\text{SiO}_2$ ), silicon nitride ( $\text{SiN}$ ), silicon carbide ( $\text{SiC}$ ), and silicon carbonitride ( $\text{SiCN}$ ).

16.-20. (Cancelled )